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Color Code:
Red – Plasma Etching
Blue – Advanced Devices

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US Patent Nr.	Title	Assignee	Filed	Date of Patent
6,517,670	Etching and cleaning apparatus	Matsushita Electric Industrial Co.	7/11/01	2/11/03
6,518,075	Method of forming S/D extension regions and pocket regions based on formulated relationship between design and measured values of gate length	NEC Corporation	4/17/01	2/11/03
6,518,112	High performance, low power vertical integrated CMOS devices	International Business Machines Corporation	7/6/01	2/11/03
6,518,133	Method for fabricating a small dimensional gate with elevated source/drain structures	Chartered Semiconductor Manufacturing	4/24/02	2/11/03
6,518,134	Method for fabricating a semiconductor device with an air tunnel formed in the lower part of a transistor channel	Hynix Semiconductor Inc.	12/21/01	2/11/03
6,518,154	Method of forming semiconductor devices with differently composed metal-based gate electrodes	Advanced Micro Devices, Inc.	3/21/01	2/11/03
6,518,191	Method for etching organic film, method for fabricating semiconductor device and pattern formation method	Matsushita Electric Industrial Co.	3/6/01	2/11/03

6,518,195	Plasma reactor using inductive RF coupling, and processes	Applied Materials Inc.	2/15/00	2/11/03
6,518,616	Vertical gate top engineering for improved GC and CB process windows	International Business Machines Corporation	4/18/01	2/11/03
6,518,619	Virtual-ground, split-gate flash memory cell arrangements and method for producing same	Koninklijke Philips Electronics N.V.	12/19/00	2/11/03
6,518,631	Multi-Thickness silicide device formed by succesive spacers	Advanced Micro Devices, Inc.	4/2/01	2/11/03
6,518,634	Strontium nitride or strontium oxynitride gate dielectric	Motorola, Inc.	9/1/00	2/11/03
6,521,082	Magnetically enhanced plasma apparatus and method with enhanced plasma uniformity and enhanced ion energy control	Applied Materials Inc.	4/16/02	2/18/03
6,521,539	Selective etch method for selectively etching a multi-layer stack layer	Chartered Semiconductor Manufacturing Ltd.	5/3/99	2/18/03
6,521,959	SOI semiconductor integrated circuit for eliminating floating body effects in SOI MOSFETs and method of fabricating the same	Samsung Electronics Co.	2/13/01	2/18/03
6,523,493	Ring-shaped high-density plasma source and method	Tokyo Electron Limited	8/1/00	2/25/03
6,524,430	Apparatus for fabricating a semiconductor device	Jusung Engineering Co.	9/21/00	2/25/03
6,524,432	Parallel-plate electrode plasma reactor having an inductive antenna and adjustable radial distribution of plasma ion density	Applied Materials Inc.	3/30/00	2/25/03
6,524,963	Method to improve etching of organic-based, low dielectric constant materials	Chartered Semiconductor Manufacturing Ltd.	10/20/99	2/25/03

6,525,338	Semiconductor substrate, field effect transistor, method of forming SiGe layer and method of forming strained Si layer using same, and method of manufacturing field effect transistor	Mitsubishi Materials Corporation	7/31/01	2/25/03
6,525,378	Raised S/D region for optimal silicidation to control floating body effects in SOI devices	Advanced Micro Devices, Inc.	6/13/01	2/25/03
6,528,376	Sacrificial spacer layer method for fabricating field effect transistor (FET) device	Taiwan Semiconductor Manufacturing Co.	11/30/01	3/4/03
6,528,399	MOSFET transistor with short channel effect compensated by the gate material	STMicroelectronics, S.A.	6/29/00	3/4/03
6,528,856	High dielectric constant metal oxide gate dielectrics	Intel Corporation	12/15/98	3/4/03
6,531,365	Anti-spacer structure for self-aligned independent gate implantation	International Business Machines Corporation	6/22/01	3/11/03
6,531,380	Method of fabricating T-shaped recessed polysilicon gate transistors	Chartered Semiconductor Manufacturing Ltd.	10/3/01	3/11/03
6,531,404	Method of etching titanium nitride	Applied Materials Inc.	8/4/00	3/11/03
6,531,781	Fabrication of transistor having elevated source-drain and metal silicide	Vanguard International Semiconductor Corporation	12/13/00	3/11/03
6,534,411	Method of high density plasma metal etching	Advanced Micro Devices, Inc.	4/13/00	3/18/03
6,534,839	Nanomechanical switches and circuits	Texas Instruments Incorporated	11/9/00	3/18/03
6,537,918	Method for etching silicon oxynitride and dielectric antireflection coatings	Applied Materials Inc.	7/31/01	3/25/03
6,537,920	Formation of vertical transistors using block copolymer lithography	Advanced Micro Devices, Inc.	3/16/01	3/25/03

6,538,273	Ferroelectric transistor and method for fabricating it	Infineon Technologies AG	5/4/01	3/25/03
6,534,41	Control of patterned etching in semiconductor features	Applied Materials Inc.	4/11/00	3/18/03